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Charge noise in ballistic multiwalled carbon nanotube transistors

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We report an experimental noise study of intermediate sized ballistic semiconducting multiwalled carbon nanotube (MWNT) devices. In this channel limited devices with no significant Schottky barriers(SB) the noise is shown to originate from the intrinsic potential fluctuations of charge traps in the gate dielectric. The gate dependence of normalized noise can be explained using a charge noise model. The noise behavior indicates that intermediate sized MWNTs are found to act like single wall carbon nanotube devices with negligible Schottky barriers. The study bridges the gap in the noise literature for SWNTs and large diameter MWNTs and has important implications in the design of channel limited nanoscale FETs using nanowires and nanotubes.

Low frequency noise properties of nanoscale electronic devices is quite distinct from the ubiquitous silicon devices. In the diffusive regime low frequency noise follows the empirical Hooges's relation which predicts a N_c^{-1} scaling of noise magnitude [1], where N_c is the number of charge carriers. The N_c^{-1} scaling, however, breaks down for ballistic nanoscale field effect transistors (FETs). In this regime the definition of N_c becomes unclear as the charge transport is no longer diffusive in which case Hooge's relation becomes inapplicable. In spite of that the low frequency noise have been routinely interpreted using Hooge's relations in literature even though the transport characteristics were explained using the ballistic transport models [2]. The problem was resolved due to Tersoff [3] where it was proposed that in nanoscale ballistic devices low frequency noise arises due to modulation of transmission due to potential fluctuations from charge traps in the dielectric and independent of the number of charge carriers. While the validity of the model has been checked through investigations for Schottky barrier[2] and liquid gated[4] SWCNT devices, no study was done in purely channel limited ballistic nanoscale devices.

For the study of noise in ballistic nanostructures multiwalled carbon nanotubes (MWNTs) can be quite useful as they have negligible Schottky barriers. However, owing to large diameters (over 20 nm) and structural disorder in the tubes, the transport through the channel is predominantly diffusive [5, 6]. For semiconducting nanotubes the band gap is inversely proportional to tube's diameter[7] as $E_g = \alpha/d$, where $\alpha \approx 0.7$ eV nm. The band gap thus vanishes for tubes with diameter greater than 10 nm yielding largely metallic tubes. In such a situation intermediate sized MWNTs (IS-MWNTs) i.e., diameters up to 10 nm, emerge as the ideal material as are semiconducting and have structure and properties reasonably close to SWNTs [6, 8]. By using tubes with short channel lengths compared to the inelastic scattering length and Palladium (Pd) as the contact metal [9] we obtain devices showing ballistic transport but having negligible Schottky barriers at the contacts.

In this letter we investigate low frequency noise in ballistic semiconducting intermediate sized MWNT devices. We find that the behavior of normalized noise as a function of gate voltage is consistent with the charge noise model[3]. We studied in total four different MWNT devices with tube diameters varying between 3-7 nm and the channel lengths between 130-520 nm. The studied tubes where highly conductive reaching the ballistic limit having the resistances in the range of $R = 6.2 - 18\ k\Omega$. It is hardly surprising to observe resistances lower than $R = 6.4k\Omega$ as such values have been measured in the past[11, 12] also for MWNTs. The presence of more than four conduction channel[13] in MWNTs is responsible for the existence of resistances lower than $R = 6.4k\Omega$. The IS-MWNT devices used in this work are quite unique representing a good model system for semiconducting ballistic devices. This makes it possible to compare the experimental results of semiconducting ballistic devices within the framework of the charge noise model not possible earlier due the challenges in fabricating such samples.

The MWNT devices were fabricated on top of highly doped Silicon wafer covered with 300 nm thick thermally grown SiO_2. Nanotubes (MWNT material from collaborating group [10] & Sigma-Aldrich) were mixed into (1,2)-dichloroethane and the suspension was spin deposited on the substrate leaving tubes laying randomly on top of the sample surface. The tubes were located using AFM (atomic force microscope) and standard e-beam lithography steps were used to electrically contact the nanotubes. The contact metal was chosen to be Pd in order to improve the contact resistance. Schematic of the sample setup is presented in figure 1. The transport measurements were performed in a RF-shielded room using home made dipstick at 4.2 K. Low frequency noise measurements were performed using a scheme described in ref.[14].

In nanoscale FETs, the electrostatic fluctuations from trap states in the oxide $1/f$ in nature, f being the frequency, is responsible for modulating the quantum transmission of the channel for ballistic transport. Thus in the crucial subthreshold region noise originates in the contact for the Schottky barrier devices or from the channel itself in case of purely channel limited one. The normalized

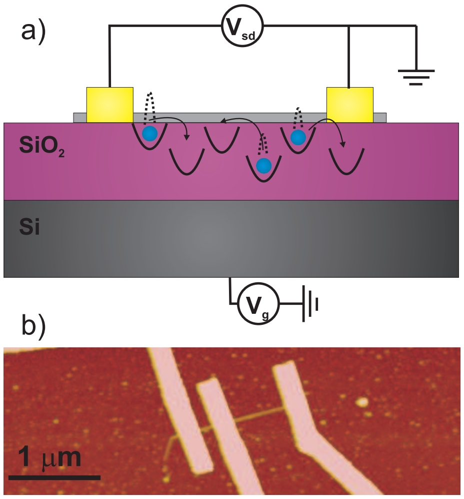

FIG. 1: (a) Schematic drawing of the sample. Charge traps fluctuate (trapping and detrapping) and can induce a potential barrier affecting the nanotube channel. Also measurement setup is drawn here. (b) An AFM image of the typical sample.

noise in the charge noise model is thus written as

$$A_I = \gamma^2 {S_g}^2 \left(\frac{dI_{sd}}{dV_g}\right)^2 + \alpha_c {I_{sd}}^2, \qquad (1)$$

where the first term is the charge noise term in the subthreshold region. The second term in equation 1 is the noise in the ON-state represented as a classical series resistor independent from the gate effects near the contacts having a noise of $\alpha_c {I_{sd}}^2$, where $\alpha = \delta {R_c}^2/{V_{sd}}^2$. Parameter S_g describes the device geometry and γ the quality of the gate oxide. In the case of Schottky barriers (SB) γ describes the number of charge traps and their proximity to the contact. When there is no SBs present e.g, a channel limited CNT-FET, γ represents the fluctuation of maximum potential along the channel.

The transport characteristics ($I-V_g$) of a Pd contacted semiconducting MWNT FET having channel length, l=130nm and diameter, d=7 nm is shown in figure 2. The device has an ON-state conductance value of (G_{ON}=6.2 kΩ) exhibiting its ballistic nature. Note the resistance lower than 6.4 kΩ. All devices studied in this work show semiconducting behavior with a gap. The gate voltage is able to cover the whole operation range from p-type to n-type conduction manifesting the ambipolar nature of all examined devices. The ON/OFF-ratio is around four orders of magnitude for the device which is sufficient for most applications[15].

The current noise power spectrum ($S_I(f)$) of the device was also recorded as a function of the gate voltage. The spectral density was a mix of $1/f$ and two level fluctuations for different values of source drain bias V_{ds}. The spectral density $S_I(f)$ has a quadratic dependence on the applied bias. Figure 2 (b) shows the normalized noise amplitude (S_I/I^2) as a function of Gate Voltage V_G for the same device. The normalized noise is minimum in the ON-state and reaches a maximum while going up to the subthreshold region (OFF-state). The monotonic nature of the gate dependent noise behavior might point towards the applicability of Hooge's empirical model as possible explanation of the noise behavior however the ballistic nature of the device effectively rules that out. The charge noise model however explains the noise behavior in the entire region as seen from figure 2 (b). Here the open circles represent the experimental noise values obtained and the solid line are fits obtained using the charge noise model.

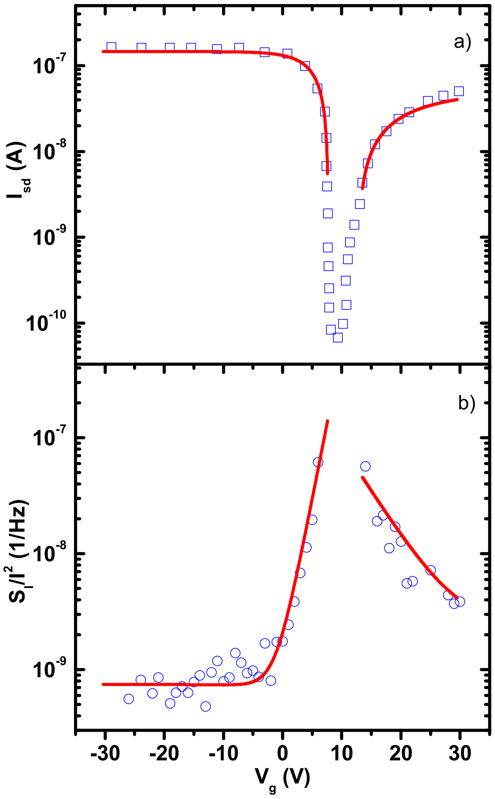

FIG. 2: (a) Source-drain current as a function of gate voltage for 2 different devices. Gate curves are measured with 1 mV source-drain voltage. (b) Normalized noise amplitude vs. gate for the same devices. Dots are the experimental data and solid lines are the fits made by using the charge noise model.

Next we compare the gate dependent noise behavior to the charge noise model proposed by Tersoff. We first deduce the charge noise term $\gamma^2 {S_g}^2 (dI_{sd}/dV_g)^2$ of equation 1 by fitting the experimental $I_{sd}(V_g)$ data with an exponential function and differentiating that analytically. The functional dependence $I_{sd}(V_g)$ for all other devices is a smooth polynomial function and the exponential fit is particular only for the present device. As we are not expecting to have noteworthy Schottky barriers at the contacts, the charge traps near the contacts make no

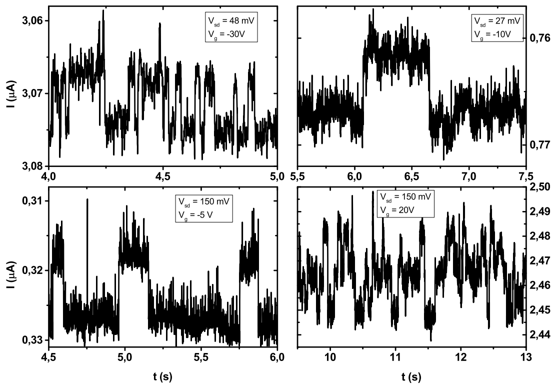

FIG. 3: RTN signals of one nanotube in different gate and source-drain voltages. The data shows random and independent configuration of RTN in respect to V_g and V_{sd}. RTN in (a) on-state (p-side) ($V_g = -30$ V and $V_{sd} = 48$ mV), (b) subthreshold region ($V_g = -10$ V and $V_{sd} = 27$ mV), (c) OFF-state and ($V_g = -5$ V and $V_{sd} = 150$ mV) (d) ON-state (n-side) ($V_g = 20$ V and $V_{sd} = 150$ mV).

contribution in producing the noise. Thus in the OFF state and subthershold region the random trap distribution in the vicinity of the device within k_BT range of energy generates a potential fluctuating in both time and space. These charge fluctuations couple electrostatically to the transistor and the fluctuation relates through random fluctuations of the gate potential[16] to produce fluctuations of the thermionic current. When turning to ON-state the highest potential barrier in the channel is not that important anymore but the channel and the contacts still contribute to the resistance and noise. In order to get good correspondence to the data also in ON-regime we add the second term $\alpha_c {I_{sd}}^2$ describing the noisy resistance in series to the analysis. Using α_c as another fitting parameter we get excellent fitting throughout the whole gate range.

The random distribution of charges in the dielectric also gets manifest in the CNT-FET as two-level fluctuations known as random telegraph signal noise (RTN). RTN is common in single walled carbon nanotube devices and have been studied both experimentally [17] and theoretically [18]. The origin of RTN have been previously attributed to the trapping and detrapping of charges in the oxide. In SWNTs even single traps have been found to have a major effect on the device currents owing to close proximity of charges to the channel. However, for MWNTs the contribution of RTN to the overall current fluctuations is expected to be much less due to larger diameters of the tubes. The noise in MWNTs is thus expected too be of $1/f$ in nature. However, we find significant Random telegraph noise in our experiments for ballistic tubes. RTN has also been found in earlier studies in large diameter MWNTs but their origin was ascribed to fluctuations from the contacts[19].

Usually RTN is characterized by a lorentzian[20, 21] power spectra ($S_I(\omega) = 4I^2\tau_{eff}^2/(1+\omega^2\tau_{eff}^2)$)) and a characteristic time given by $1/\tau_{eff} = 1/\tau_1 + 1/\tau_2$. The characteristic time reduces exponentially with applied bias[22]. At high bias the spectra thus shows an evolution from the lorentzian to $1/f$ type. In the charge noise model, occasionally fluctuating charge in close vicinity of the tube can induce RTN in a tube as illustrated in figure 1. This implies that in systems with ballistic transport, RTN (represented by γS_g in the charge noise model) should be present with no significant bias dependence as the traps are present in a random configuration in the oxide. However, in all the MWNT devices studied in this work, the experimental results point to no particular V_{sd} or V_g dependence of RTN. For some voltage values the spectra is of $1/f$ character and for some RTN is observed. There is no particular trend in voltage for the observation of RTN. In figure 3, we plot a few typical RTN at four random V_{sd} and V_g values for another tube. This tube has a diameter of 3 nm and channel length 380 nm with a typical ON state resistance of 14.8 kΩ. This observation points to the fact that fluctuation of transmission in ballistic quantum channels manifests as RTN in the ballistic MWNT devices as proposed in the charge noise model[3]. Recall that SWNTs having smaller diameters are more prone to RTN effects than larger diameter MWNT devices which have predominantly flicker noise. The large value of RTN in intermediate sized MWNTs point towards the fact that they act more like SWNTs. Moreover, the tubes used in this work are ballistic or really close to ballistic limit which is similar to SWNTs than MWNTs which are mainly diffusive owing to large disorder.

As noise in the charge noise model is given by the modulation of transmission (related to γS_g), which is directly related to the oxide quality, suggests that the crucial factor for optimizing noise properties of ballistic FET is the quality of gate oxide. Minimizing noise in such a device would require a drastic reduction in the number of charge traps in the gate oxide. It is imperative that a fully suspended structure with vacuum as dielectric would result in better low noise transistors. The absence of potential fluctuations due to the charge traps in the suspended structures can also prove useful for testing several other aspects of the charge noise model in ballistic devices.

In conclusion, we have presented the low frequency noise properties for intermediate sized ballistic semiconducting MWNT FETs without any or negligible Schottky barriers. The gate dependence of low frequency noise in these devices can be better described using a charge noise model instead of the more traditional Hooge's model for diffusive devices. Ballistic SWNTs without Schottky barriers are more difficult to fabricate than IS-MWNT devices. This makes IS-MWNTs better candidates for testing different aspects of the charge noise model. Furthermore, our study bridges the gap in the study of low frequency noise behavior in general between single and large diameter multiwalled tubes. These findings indicate that intermediate sized MWNT's can be used for potential applications in nanoelectronics instead of SWNT's, if they are more desirable for some additional reason, for example, due to their much higher mechanical rigidity.

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